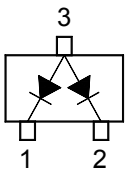
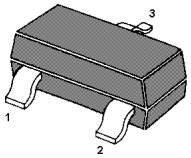
SEMICONDUCTOR

BAW56
Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance





Marking Code: **A1**
TO-236 Plastic Package

Applications

- Ultra high speed switching application

Absolute Maximum Ratings (T_a = 25℃)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage		V_{RRM}	85	V
Continuous Reverse Voltage		V_R	75	V
Forward Current (DC)	Single Diode Loaded Double Diode Loaded	I_F	215 125	mA
Repetitive Peak Forward Current		I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 ms at t = 1 μs	I_{FSM}	0.5 1 4	A
Power Dissipation		P_{tot}	350	mW
Operating Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	- 65 to + 150	℃

Characteristics at T_a = 25℃

Parameter	Symbol	Max.	Unit
Forward Voltage			
at I_F = 1 mA	V_F	715	mV
at I_F = 10 mA	V_F	855	mV
at I_F = 50 mA	V_F	1	V
at I_F = 150 mA	V_F	1.25	V
Reverse Current			
at V_R = 25 V	I_R	30	nA
at V_R = 75 V	I_R	1	μA
at V_R = 25 V, T_J = 150℃	I_R	30	μA
at V_R = 75 V, T_J = 150℃	I_R	50	μA
Diode Capacitance at V_R = 0 , f = 1 MHz	C_d	2	pF
Reverse Recovery Time at I_F = 10 mA,V_R = 6 V, I_{rr} = 1 mA, R_L = 100 Ω	t_{rr}	4	ns

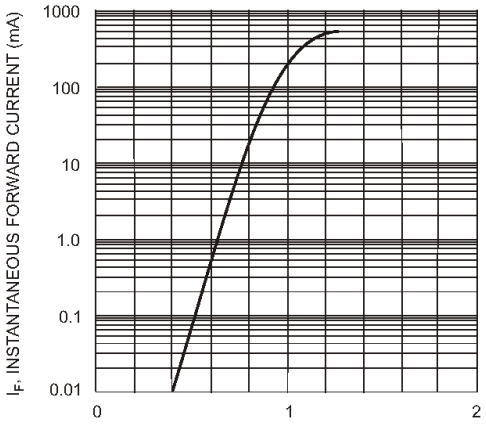


Fig. 1 Forward Characteristics

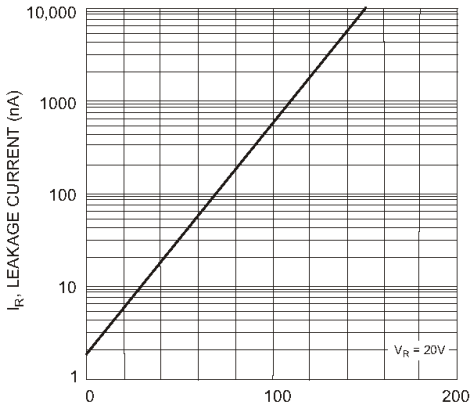


Fig. 2 Leakage Current vs Junction Temperature

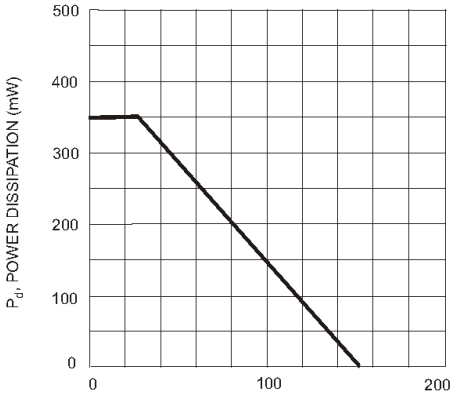


Fig. 3 Power Derating Curve, total package